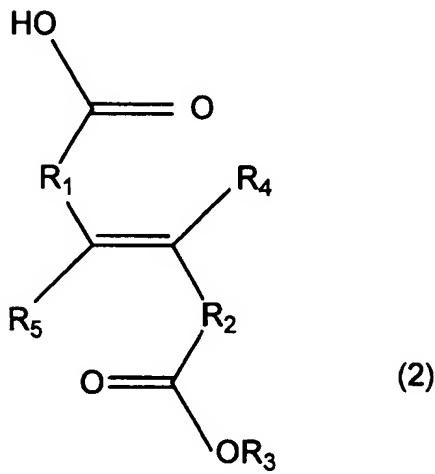
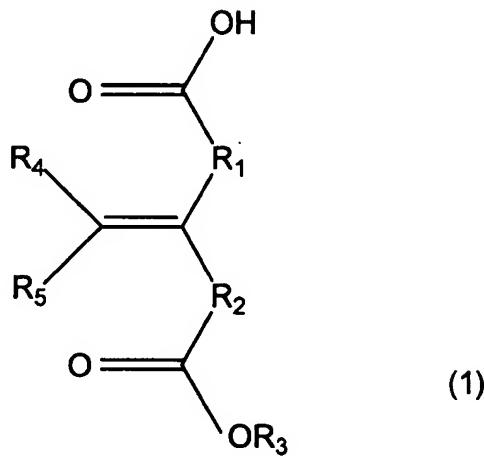


**AMENDMENTS TO THE ABSTRACT**

**Please amend the abstract as shown on the attached separate page.**

## Abstract

A negative resist composition includes a polymer having any one of dicarboxylate monoester compounds represented by the following general formulae (1) and (2) as a monomer component:



wherein, R<sub>1</sub> and R<sub>2</sub> represent alkyl chains having 0 to [5] 8 carbon atoms, R<sub>3</sub> represents a substituent having at least two or more alicyclic structures, and R<sub>4</sub> and R<sub>5</sub> represent hydrogen atoms or alkyl groups having 1 to 8 carbon atoms. A method for forming a resist pattern uses the above negative resist composition. By containing the polymer, a resistance to dry etching and a resistance to electron beam from a scanning electron microscope (SEM) are enhanced as well as a solubility in an alkali developing solution is maintained.